



DRV2511-Q1 8A車載用、ソレノイドおよび音声コイル用ハブティック・ドライバ

1 特長

- 広い動作電圧範囲(4.5V~26V)
- 30Vの電圧を処理可能
- 高い電流ドライブ(8Aピーク)
- 低い $R_{DS(on)}$ 、完全なHブリッジ出力
- フォルト保護機能内蔵
 - 短絡保護
 - 過熱保護
 - 過電圧および低電圧保護
 - 障害通知
- アナログ入力
- 専用の割り込みピン
- 下記内容でAEC-Q100認定済み
 - デバイス温度グレード1: 動作時周囲温度範囲
–40°C ~ 125°C
 - デバイスHBM ESD分類レベルH2
 - デバイスCDM ESD分類レベルC4B

2 アプリケーション

- 電磁気アクチュエータ・ドライバ
 - 音声コイル
 - ソレノイド
- 機械式ボタンの置き換え
- 車載用ハブティック・アプリケーション
 - インフォテインメント
 - 中央コンソール
 - ステアリング・ホイール
 - ドア・パネル
 - シート

3 概要

このDRV2511-Q1デバイスは、大電流のハブティック・ドライバで、ソレノイドや音声コイルなど誘導性の負荷に特化して設計されています。

出力ステージは、完全なHブリッジで構成され、8Aのピーク電流を供給できます。

DRV2511-Q1デバイスは、低電圧誤動作防止、過電流保護、過熱保護などの保護機能を備えています。

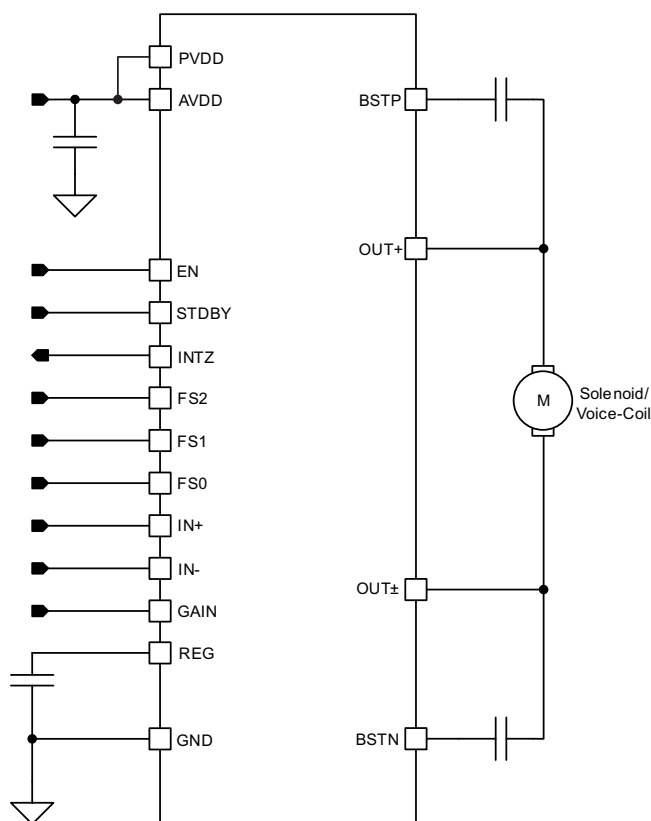
このDRV2511-Q1デバイスは車載用に認定済みです。

製品情報⁽¹⁾

型番	パッケージ	本体サイズ(公称)
DRV2511-Q1	HTSSOP (32)	11 mm x 6.20 mm

(1) 提供されているすべてのパッケージについては、巻末の注文情報を参照してください。

概略回路図



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4 改訂履歴

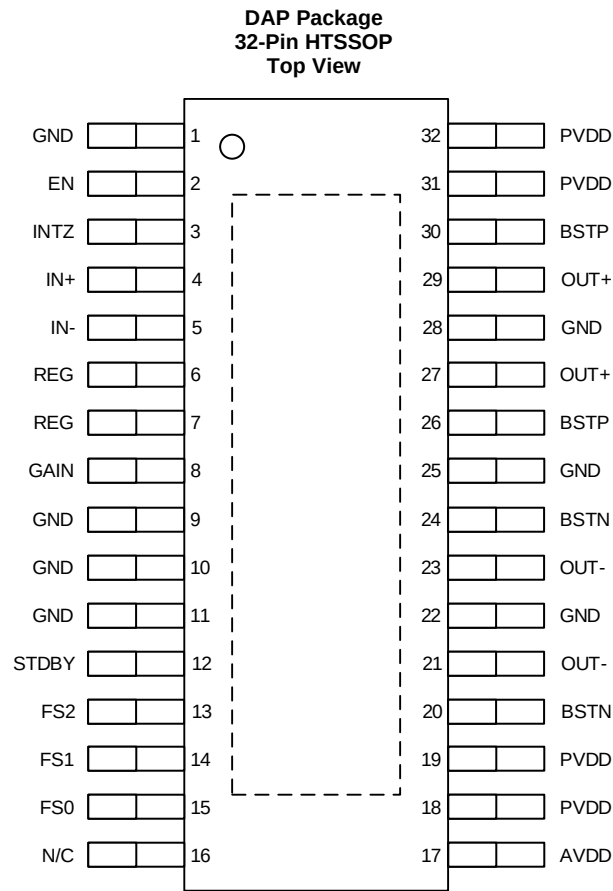
資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

2016年6月発行のものから更新

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5 Pin Configuration and Functions



Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
GND	1, 9, 10, 11, 22, 25, 28	P	Ground.
EN	2	I	Device enable pin.
INTZ	3	O	General fault reporting. Open drain. INTZ = High, normal operation INTZ = Low, fault condition
IN+	4	I	Positive differential input.
IN-	5	I	Negative differential input.
REG	6, 7	P	Internally generated gate voltage supply. Not to be used as a supply or connected to any component other than a 1 μ F X7R ceramic decoupling capacitor and the MODE resistor divider.
GAIN	8	I	Selects Gain.
STDBY	12	I	Standby pin.
FS2	13	I	Output switching frequency selection.
FS1	14	I	Output switching frequency selection.
FS0	15	I	Output switching frequency selection.
N/C	16	N/C	Pin should be left floating.
AVDD	17	P	Analog Supply, can be connected to VBAT for single power supply operation.
PVDD	18, 19, 31, 32	P	Power supply.
BSTN	20, 24	P	Boot strap for negative output, connect to 220 nF X5R, or better ceramic cap to OUT-.
OUT-	21, 23	O	Negative output.
BSTP	26, 30	P	Boot strap for positive output, connect to 220 nF X5R, or better ceramic cap to OUT+.

Pin Functions (continued)

PIN		TYPE	DESCRIPTION
NAME	NO.		
OUT+	27, 29	O	Positive output.
Thermal Pad or PowerPAD™		G	Connect to GND for best system performance. If not connected to GND, leave floating.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
Supply voltage	PVDD, AVDD	−0.3	30	V
Input voltage, V_I	IN+, IN-	−0.3	6.3	V
	GAIN	−0.3	VREG + 0.3	
	EN	−0.3	PVDD + 0.3	
Current	DC current on PVDD, GND, OUT+, OUT-	−8	8	A
Operating free-air temperature, T_A		−40	125	°C
Storage temperature range, T_{stg}		−50	150	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

		MIN	MAX	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	−2000	2000	V
	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	−450	450	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
VDD	Supply voltage. PVDD, AVDD.	4.5		26	V
V_{IH}	High-level input voltage. STDBY, EN, FS0, FS1, FS2.	2			V
V_{IL}	Low-level input voltage. STDBY, EN, FS0, FS1, FS2.			0.8	V
V_{OL}	Low-level output voltage. INTZ, $R_{PULL-UP}$ = 100 k Ω , PVDD = 26 V.			0.8	V
I_{IH}	High-level input current. STDBY, EN, FS0, FS1, FS2. (V_I = 2 V, PVDD = 26 V).			50	μ A
R_L	Minimum load Impedance.		1.65		Ω
L_o	Output-filter Inductance.	1			μ H

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		DRV2511-Q1	UNIT
		DAP	
		32 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	32.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	17.2	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

Thermal Information (continued)

THERMAL METRIC ⁽¹⁾		DRV2511-Q1	UNIT
		DAP	
		32 PINS	
$R_{\theta JB}$	Junction-to-board thermal resistance	17.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.4	°C/W
ψ_{JB}	Junction-to-board characterization parameter	17.2	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	1	°C/W

DRV2511-Q1

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6.5 Electrical Characteristics

$T_A = 25^\circ\text{C}$, $AVCC = PVDD = 12\text{ V}$, $R_L = 5\ \Omega$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$ V_{OS} $	Output offset voltage (measured differentially)	$V_I = 0\text{ V}$, Gain = 36 dB		1.5	15	mV
I_{VDD}	Quiescent supply current	No load or filter		20		mA
$I_{VDD(SD)}$	Quiescent supply current in shutdown mode	No load or filter		35		μA
$I_{VDD(STD BY)}$	Quiescent supply current in standby mode	No load or filter		11		mA
$r_{DS(on)}$	Drain-source on-state resistance, measured pin to pin	$T_J = 25^\circ\text{C}$		60		$\text{m}\Omega$
G	Gain	$R1 = \text{open}$, $R2 = 20\text{ k}\Omega$	19	20	21	dB
		$R1 = 100\text{ k}\Omega$, $R2 = 20\text{ k}\Omega$	25	26	27	
		$R1 = 100\text{ k}\Omega$, $R2 = 39\text{ k}\Omega$	31	32	33	dB
		$R1 = 75\text{ k}\Omega$, $R2 = 47\text{ k}\Omega$	35	36	37	
V_{REG}	Regulator voltage		6.4	6.9	7.4	V
BW	Full Power Bandwidth			60		kHz
V_O	Output voltage (measured differentially)	Measured at $PVDD = 26\text{V}$		50		V
PSRR	Power supply ripple rejection	200 mVpp ripple at 1 kHz, Gain = 20 dB		–70		dB
CMRR	Common-mode rejection ratio			–56		dB
f_{OSC}	Oscillator frequency (with PWM duty cycle < 96%)	$FS2 = 0$, $FS1 = 0$, $FS0 = 0$	376	400	424	kHz
		$FS2 = 0$, $FS1 = 0$, $FS0 = 1$	470	500	530	
		$FS2 = 0$, $FS1 = 1$, $FS0 = 0$	564	600	636	
		$FS2 = 0$, $FS1 = 1$, $FS0 = 1$	940	1000	1060	
		$FS2 = 1$, $FS1 = 0$, $FS0 = 0$	1128	1200	1278	
	Power-on threshold			4.1		V
	Power-off threshold			28		V
	Thermal trip point			150		$^\circ\text{C}$
	Thermal hysteresis			15		$^\circ\text{C}$
	Over-current trip point			13		A
	Over-voltage trip point			28		V

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{on-sd}	Turn-on time from shutdown to waveform	EN = Low to High, STBY = Low		10		ms
t_{OFF-sd}	Turn-off time	EN = High to Low		5		μs
$t_{on-stdby}$	Turn-on time from standby to waveform	EN = High, STBY = High to Low		6		μs

6.7 Typical Characteristics

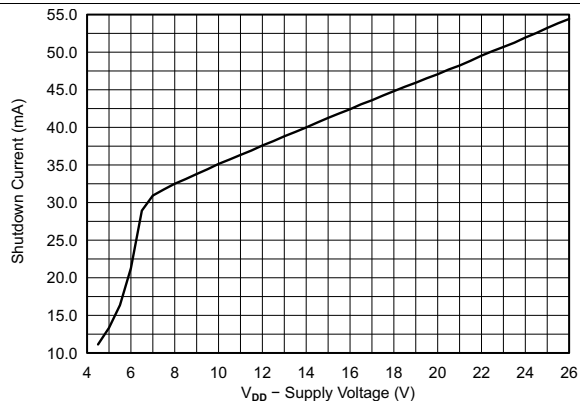


図 1. Shutdown Current vs VDD Voltage

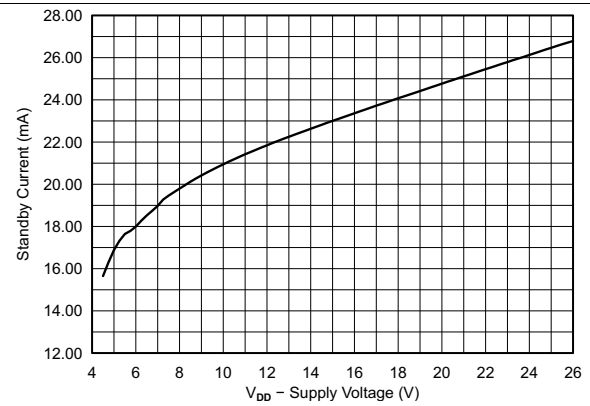


図 2. Standby Current vs VDD Voltage

7 Detailed Description

7.1 Overview

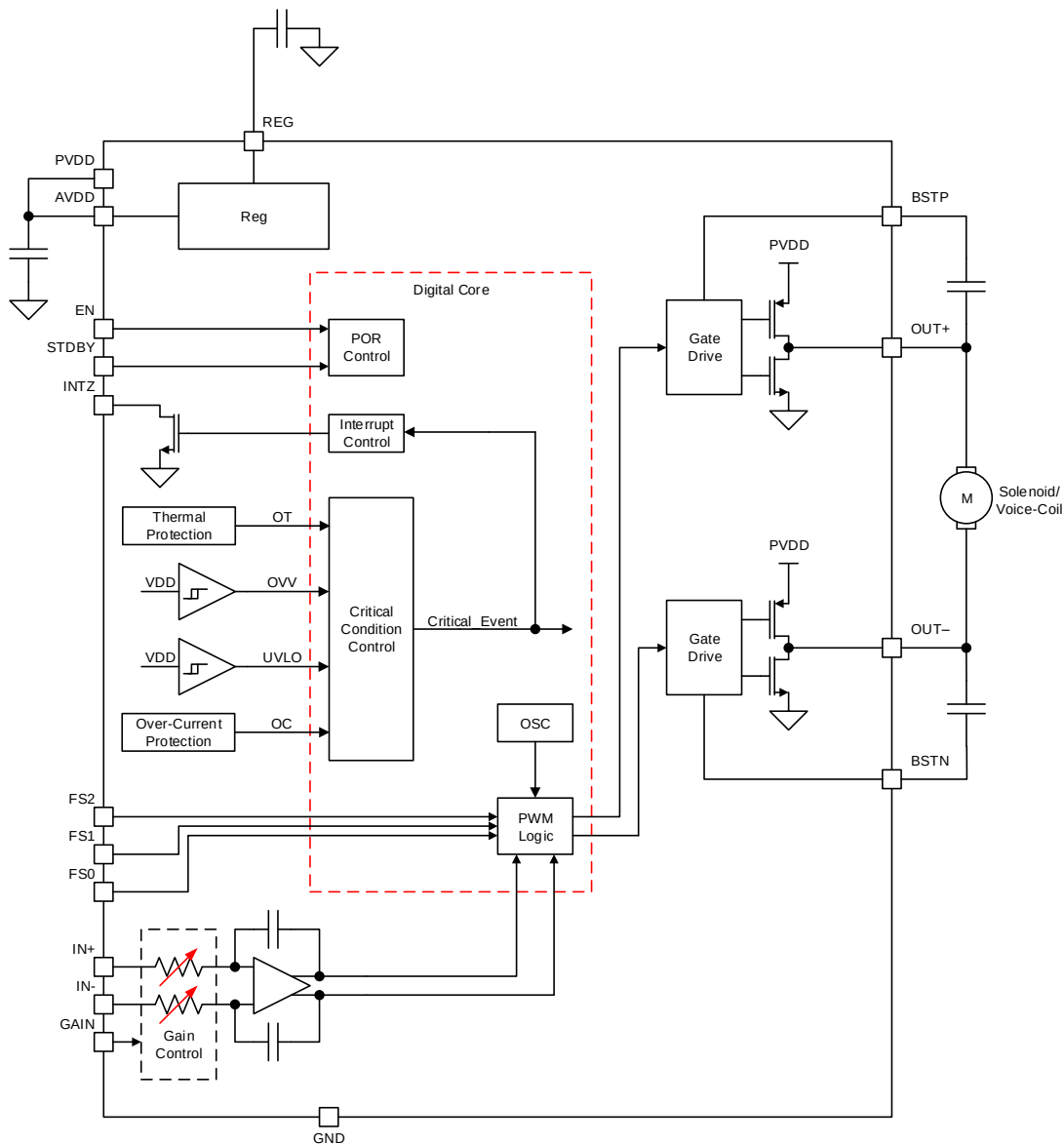
The DRV2511-Q1 device is a high current haptic driver specifically designed for inductive loads, such as solenoids and voice coils.

The output stage consists of a full H-bridge capable of delivering 8 A of peak current.

The design uses an ultra-efficient switching output technology developed by Texas Instruments, but with features added for the automotive industry. The DRV2511-Q1 device provides protection functions such as undervoltage lockout, over-current protection and over-temperature protection. This technology allows for reduced power consumption, reduced heat, and reduced peak currents in the electrical system.

The DRV2511-Q1 device is automotive qualified.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Analog Input and Configurable Pre-amplifier

The DRV2511-Q1 device features a differential input stage that cancels common-mode noise that appears on the inputs. The DRV2511-Q1 device also features four gain settings that are configurable via external resistors.

表 1. Gain Configuration Table

GAIN	R1	R2	INPUT IMPEDANCE
20 dB	5.6 k Ω	open	60 k Ω
26 dB	20 k Ω	100 k Ω	30 k Ω
32 dB	39 k Ω	100 k Ω	15 k Ω
36 dB	47 k Ω	75 k Ω	9 k Ω

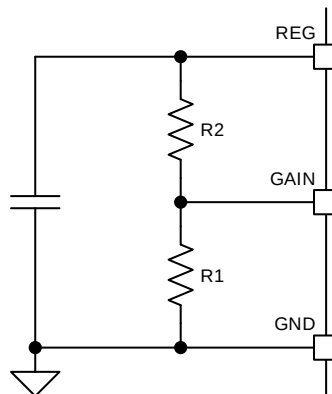


图 3. Gain Configuration

7.3.2 Pulse-Width Modulator (PWM)

The DRV2511-Q1 device features BD modulation scheme with high bandwidth, low noise, low distortion, and excellent stability.

The BD modulation scheme allows for smaller ripple currents through the load. Each output switches from 0 V to the supply voltage. With no input, the OUT+ and OUT- pins are in phase with each other so that there is little or no current in the load. For positive differential inputs, the duty cycle of OUT+ is greater than 50% and the duty cycle of OUT- is lower than 50% for a positive differential output voltage. The opposite is true for negative differential inputs. The voltage across the load sits at 0 V throughout most of the switching period, reducing the switching current, which reduces the I^2R losses in the load.

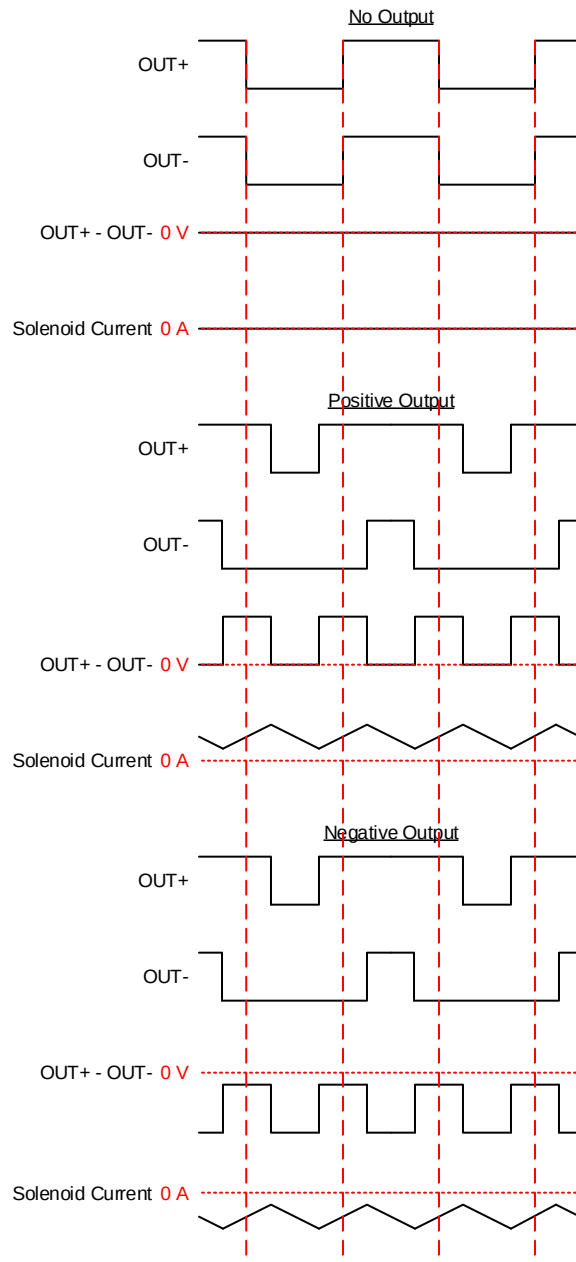


图 4. BD Mode Modulation

7.3.3 Designed for low EMI

The DRV2511-Q1 device design has minimal parasitic inductances due to the short leads on the package. This dramatically reduces EMI that results from current passing from the die to the system PCB. The design incorporates circuitry that optimizes output transitions that causes EMI. Follow the recommended design requirements in the [Design Requirements](#) section.

7.3.4 Device Protection Systems

The DRV2511-Q1 device features a complete set of protection circuits carefully designed to protect the device against permanent failures due to shorts, over-temperature, over-voltage, and under-voltage scenarios. The INTZ pin signals if an error is detected.

表 2. Fault Reporting Table

FAULT	TRIGGERING CONDITION	INTZ	ACTION	LATCH?
Over-current	Output short or short to PVDD or GND	pulled low	output in high impedance	Latched
Over-temperature	$T_j > 150\text{ }^{\circ}\text{C}$	pulled low	output in high impedance	Latched
Under-voltage	PVDD < 4.5 V	-	output in high impedance	Self-clearing
Over-voltage	PVDD > 27 V	-	output in high impedance	Self-clearing

When the "Latched" conditions happen, the device must be reset with the EN signal in order to clear the fault. If automatic recovery from these conditions is desired, connect the INTZ pin directly to the EN pin. This allows the INTZ pin function to automatically drive the EN pin low which clears the latched condition.

7.4 Device Functional Modes

The DRV2511-Q1 device has multiple power states to optimize power consumption.

7.4.1 Operation in Shutdown Mode

The NRST pin of the DRV2511-Q1 device puts the device in a shutdown mode. When NRST is asserted (logic low), all internal blocks of the device are off to achieve ultra low power.

7.4.2 Operation in Standby Mode

The STDBY pin of the DRV2511-Q1 device puts the device in a standby mode. When STDBY is asserted (logic high), some internal blocks of the device are off to achieve low power while preserving the ability to wake up quickly to achieve low latency waveform playback.

7.4.3 Operation in Active Mode

The DRV2511-Q1 device is in active mode when it has a valid supply, and it is not in either shutdown or standby modes. In this mode the DRV2511-Q1 device is fully on and reproducing at the output the input times the gain.

7.5 Programming

7.5.1 Gain

The DRV2511-Q1 device has a configurable gain that is controlled through external resistors. Please see the Analog Input and Configurable Pre-amplifier section for more details.

Typical Applications (continued)

表 3. Component Requirements Table

COMPONENT	DESCRIPTION	SPECIFICATION	TYPICAL VALUE
C1	Supply capacitor	Capacitance	22 μF and 0.1 μF for PVDD & AVDD
C2/C3	Boost capacitor	Capacitance	0.22 μF
C4/C5	Output snubber capacitor	Capacitance	470 pF
C6	Regulator capacitor	Capacitance	1 μF
C9	Input decoupling capacitor	Capacitance	0.1 μF
R1/R2	Output snubber resistor	Resistance	3.3 Ω
R _(PU)	Pull-up resistor	Resistance	100 kΩ

8.2.1.2 Detailed Design Procedure

8.2.1.2.1 Optional Components

Note that in the diagrams, there are a few optional external components. These optional external components may be needed in the application to meet EMI/EMC standards and specifications by filters necessary frequency spectrums.

8.2.1.2.2 Capacitor Selection

A bulk bypass capacitor should be mounted between VBAT and GND. The capacitance needs to be >22 uF with a X5R or better rating on the power pins to GND. Also include two ceramic capacitors in the ranges of 220 pF to 1 uF and 100 nF to 1 uF. The bootstrap capacitors, BSTA and BSTB, should be 220-nF ceramic capacitors of quality X5R or better rated for at least the maximum rating of the pin.

8.2.1.2.3 Solenoid Selection

The DRV2511-Q1 solenoid driver can accommodate a variety of solenoids. Solenoids should have an equivalent resistance of 1.6 Ω or greater. Solenoids with lower resistances are prone to driving high currents. A maximum peak current of 8-A should not be exceeded. The DRV2511-Q1 will go into a shutdown mode to protect itself from overcurrent.

8.2.1.2.4 Output Filter Considerations

The output filter is optional and is mainly for limiting peak currents. A second-order Butterworth low-pass filter with the cut-off frequency set to a few kilohertz should be sufficient. See 式 2, 式 3, and 式 4 for example filter design.

$$H(s) = \frac{1}{s^2 + \sqrt{2}s + 1} \quad (1)$$

$$L_x = \frac{\sqrt{2} \times R_L}{2\omega_0} \quad (2)$$

$$2 \times C_F = \frac{\sqrt{2}}{2 \times \frac{R_L}{2} \times \omega_0} \quad (3)$$

$$\omega_0 = 2\pi \times f \quad (4)$$

8.2.1.3 Application Curves

These application curves were taken using an HA200 solenoid with a 100-g mass, and the acceleration was measured using the DRV-AAC16-EVM accelerometer. The following scales apply to the graphs:

- Output Differential Voltage scale is shown on the plots at 5-V/div
- Acceleration scale is 5.85-G/div
- Current scale is 2-A/div

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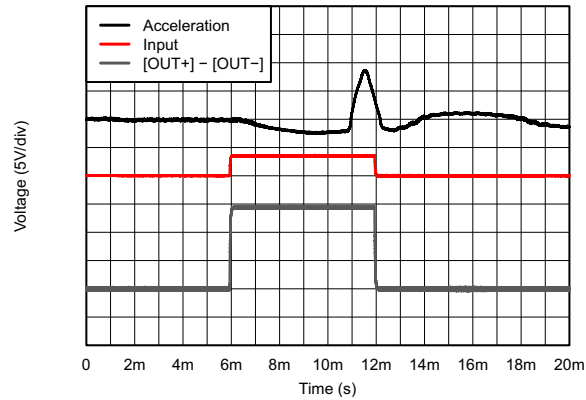


Figure 6. Voltage and Acceleration vs Time (Input Square Wave)

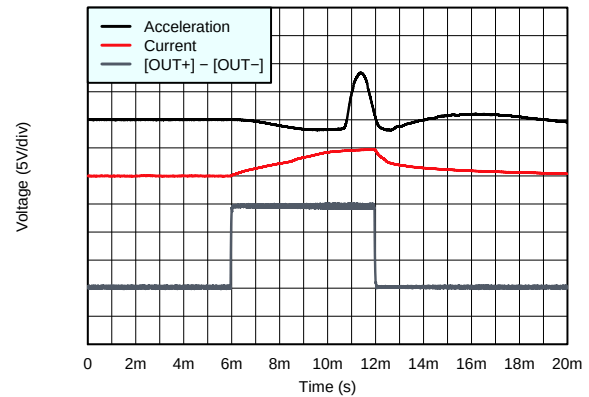


Figure 7. Voltage and Acceleration vs Time (Square Wave)

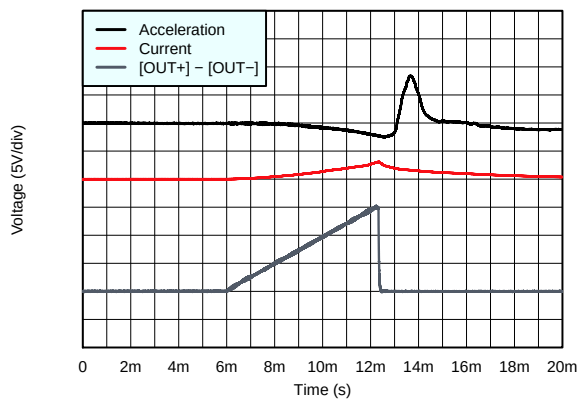


Figure 8. Voltage and Acceleration vs Time (Ramp Wave)

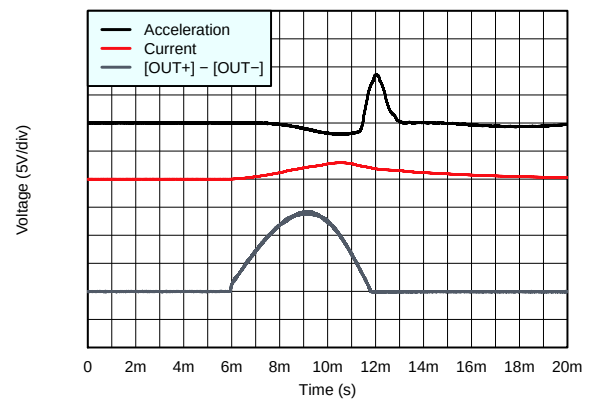


Figure 9. Voltage and Acceleration vs Time (1/2 Sine Wave)

8.2.1.4 Differential Input Diagram

To use the DRV2511-Q1 with a differential input source, apply both inputs differentially from a control source (GPIO, DAC, etc...).

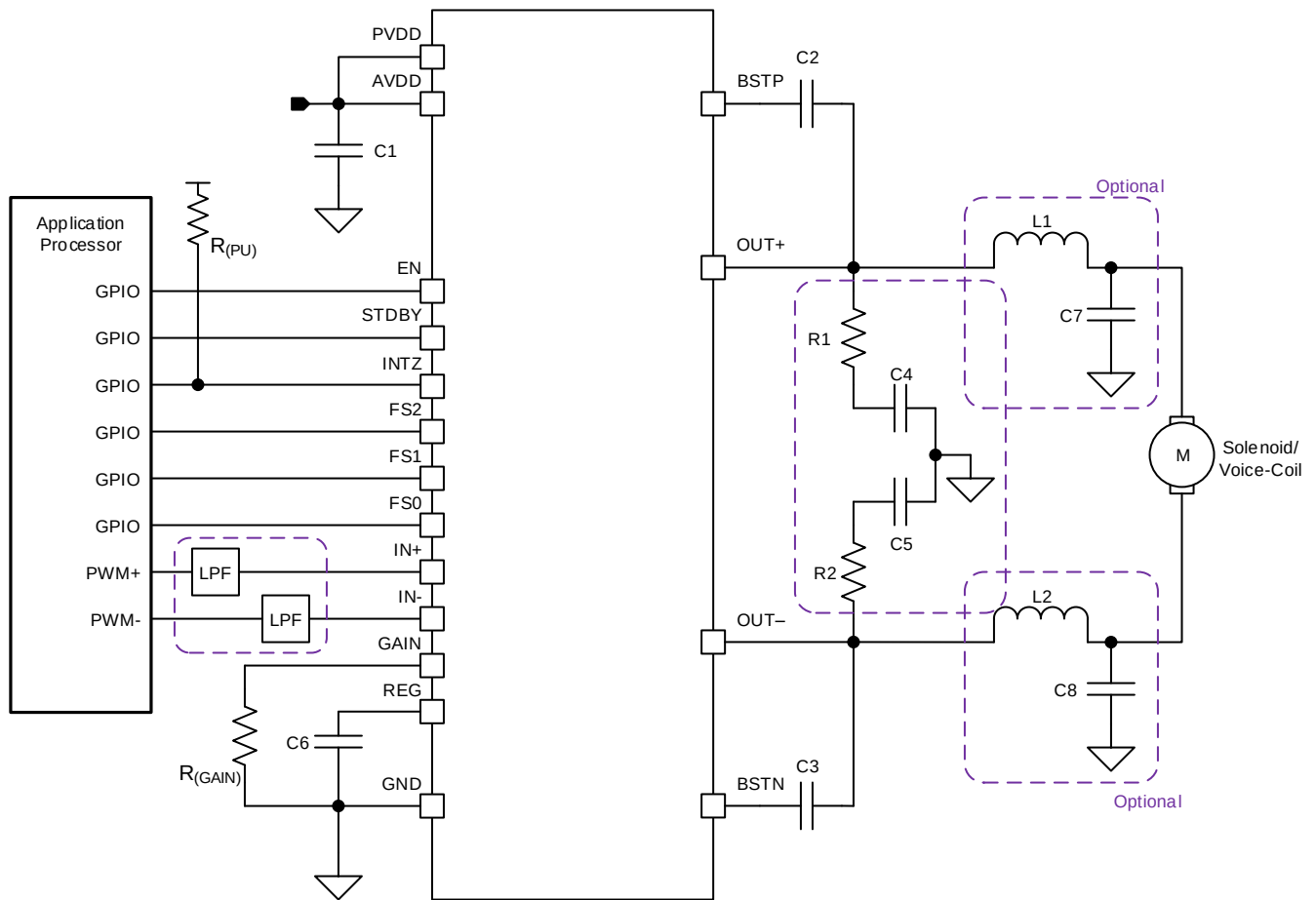


FIG 10. Typical Application Schematic

9 Power Supply Recommendations

The DRV2511-Q1 device operates from 4.5 V - 26 V and this supply should be able to handle high surge currents in order to meet the high current draws for haptics effects. Additionally the DRV2511-Q1 should have 22- μ F and 0.1- μ F ceramic capacitors near the PVDD & AVDD pins for additional decoupling from trace routing.

10 Layout

10.1 Layout Guidelines

The EVM layout optimizes for thermal dissipation and EMC performance. The DRV2511-Q1 device has a thermal pad down, and good thermal conduction and dissipation require adequate copper area. Layout also affects EMC performance. It is best practice to use the same/similar layout as shown below in the DRV2511Q1EVM.

10.2 Layout Example

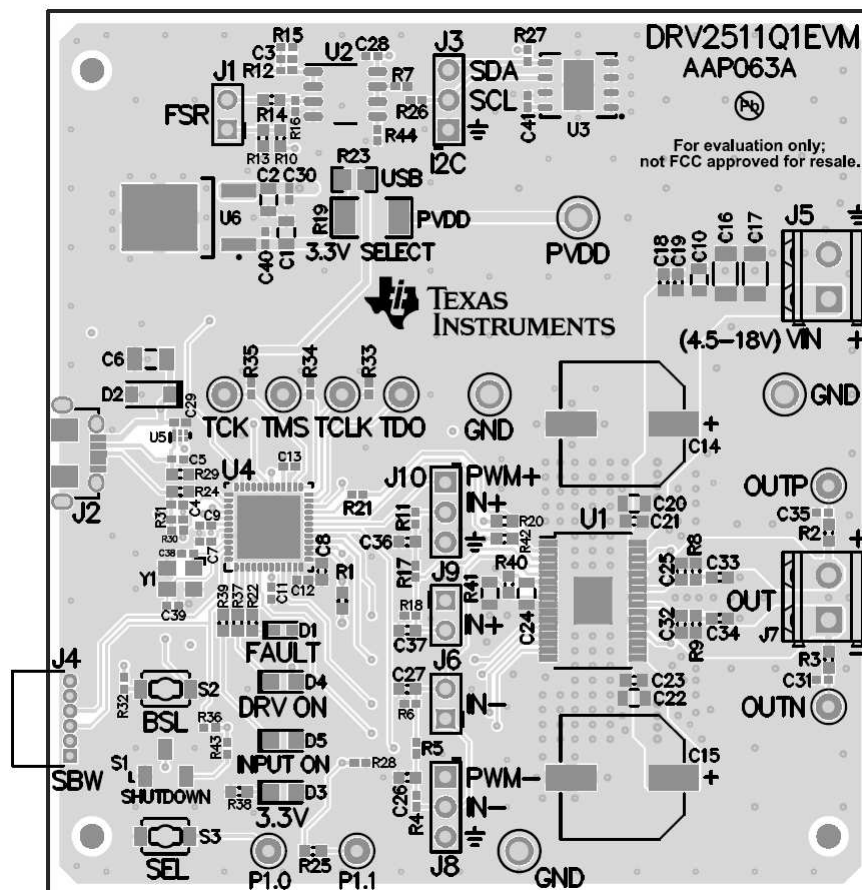


图 11. DRV2511-Q1 EVM

11 デバイスおよびドキュメントのサポート

11.1 デバイス・サポート

11.1.1 デベロッパー・ネットワークの製品に関する免責事項

デベロッパー・ネットワークの製品またはサービスに関するTIの出版物は、単独またはTIの製品、サービスと一緒に提供される場合に関係なく、デベロッパー・ネットワークの製品またはサービスの適合性に関する是認、デベロッパー・ネットワークの製品またはサービスの是認の表明を意味するものではありません。

11.2 商標

PowerPAD is a trademark of Texas Instruments.

11.3 静電気放電に関する注意事項



これらのデバイスは、限定的なESD(静電破壊)保護機能を内蔵しています。保存時または取り扱い時は、MOSゲートに対する静電破壊を防止するために、リード線同士をショートさせておくか、デバイスを導電フォームに入れる必要があります。

11.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。これらの情報は、指定のデバイスに対して提供されている最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV2511QDAPRQ1	ACTIVE	HTSSOP	DAP	32	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	DRV2511Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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GENERIC PACKAGE VIEW

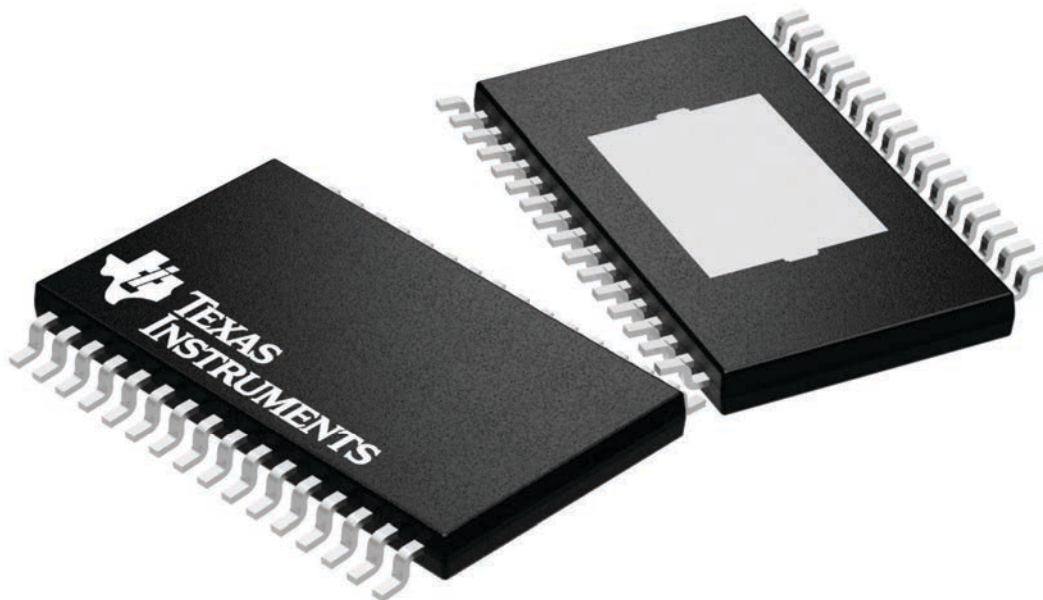
DAP 32

PowerPAD™ TSSOP - 1.2 mm max height

8.1 x 11, 0.65 mm pitch

PLASTIC SMALL OUTLINE

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



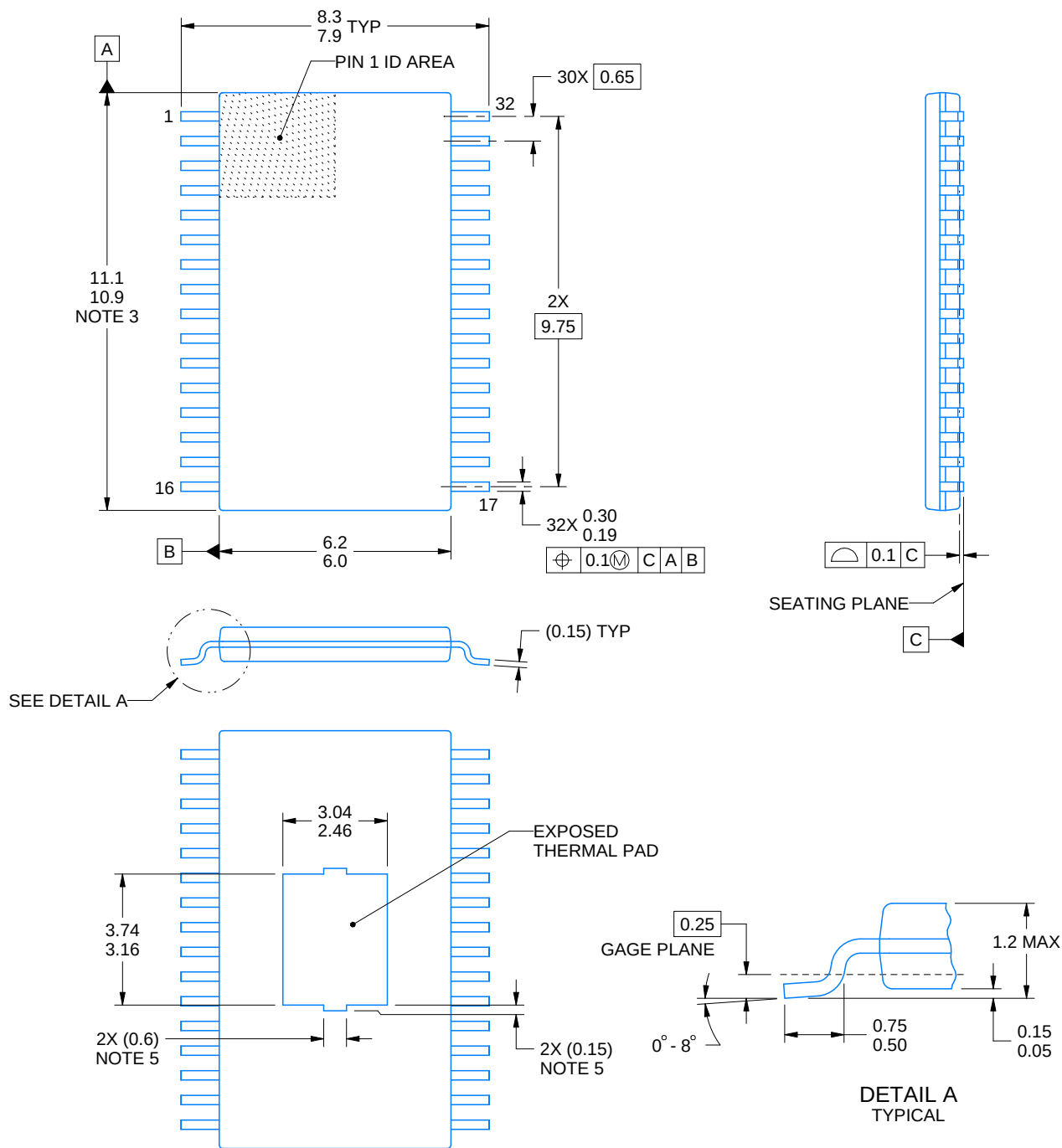
4225303/A



DAP0032C

PowerPAD™ TSSOP - 1.2 mm max height

PLASTIC SMALL OUTLINE



4223691/A 05/2017

NOTES:

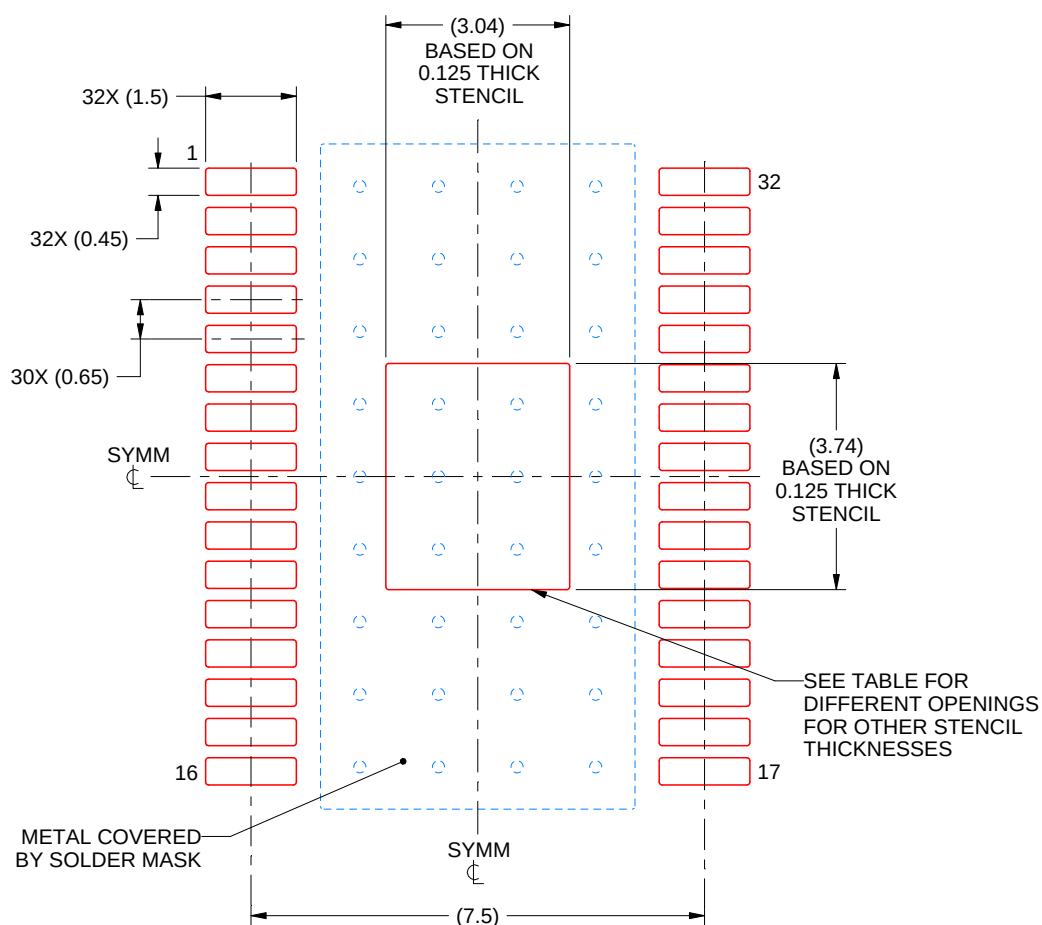
PowerPAD is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-153.
5. Features may differ and may not be present.

DAP0032C

PowerPAD™ TSSOP - 1.2 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
EXPOSED PAD
100% PRINTED SOLDER COVERAGE BY AREA
SCALE:8X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	3.40 X 4.18
0.125	3.04 X 3.74 (SHOWN)
0.15	2.78 X 3.41
0.175	2.57 X 3.16

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NOTES: (continued)

10. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
11. Board assembly site may have different recommendations for stencil design.

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